DIC HW#4

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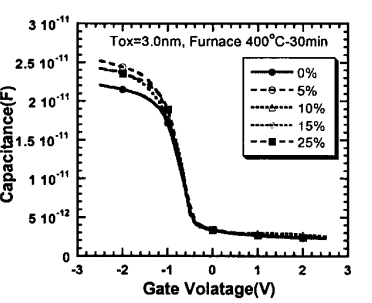
Reference :

Dielectric material : TaSixNy/SiO2 stack.

tox : 3.0nm

Temperature : 400K

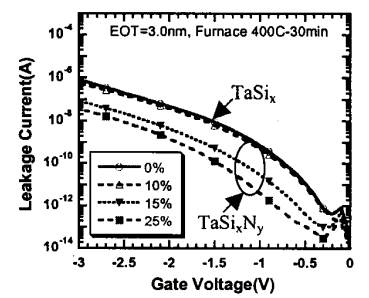
C-V characteristics



* Graph for N concentration of Dielectric material.

When the gate voltage is increased, the capacitance is decreased.

Gate voltage vs. Leakage current



When the gate voltage is decreased, the leakage current is increased.